

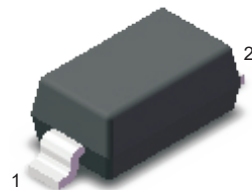


1N5817W~1N5819W Schottky Barrier Diodes

Features

- High current capability
- Low power loss, high efficiency
- Guarding for overvoltage protection

SOD-123



1.Cathode —  2.Anode

Marking Code :

1N5817W: SJ

1N5817W: SK

1N5817W: SL

Maximum Ratings and Electrical Characteristics

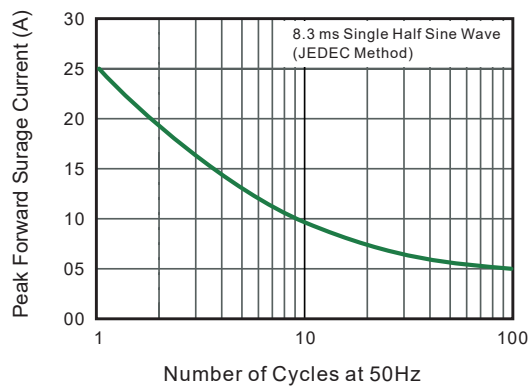
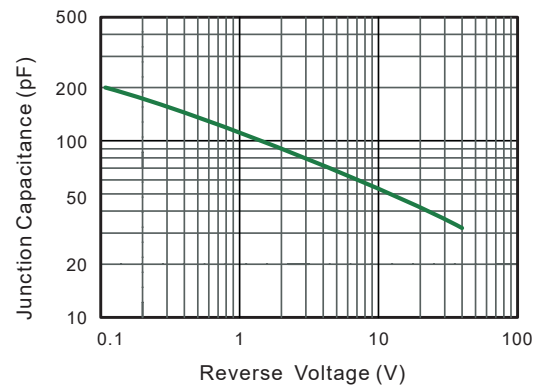
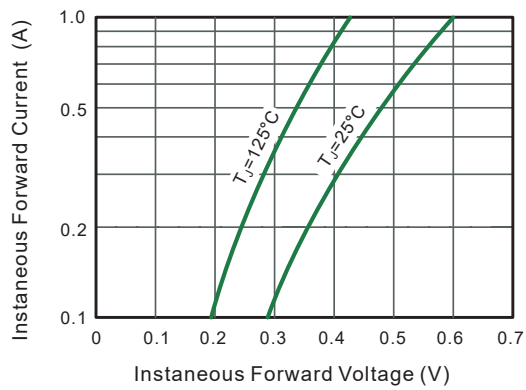
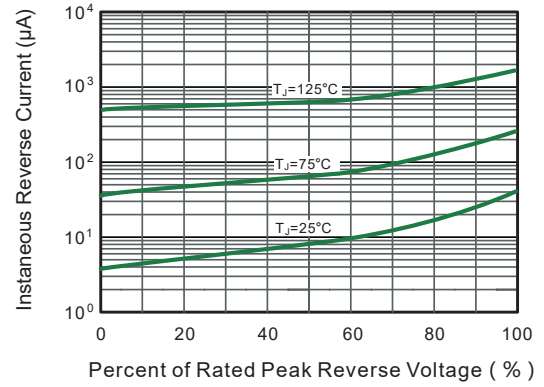
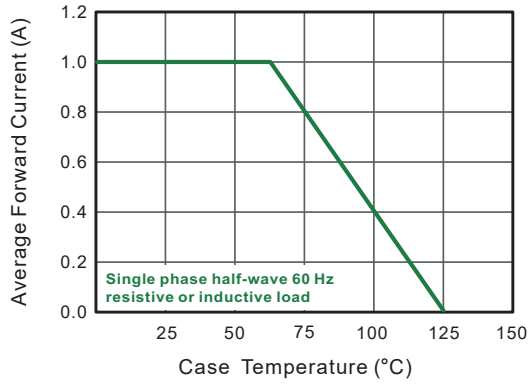
Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbols	1N5817W	1N5818W	1N5819W	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	V
Maximum RMS Voltage	V_{RMS}	14	21	28	V
Maximum DC Blocking Voltage	V_{DC}	20	30	40	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1.0			A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	25			A
Maximum Instantaneous Forward Voltage at 1 A at 3 A	V_F	0.45 0.75	0.55 0.875	0.6 0.9	V
Maximum DC Reverse Current at Rated DC Blocking Voltage at $T_A = 25^\circ\text{C}$ at $T_A = 100^\circ\text{C}$	I_R	1 10			mA
Typical Junction Capacitance	C_j	110			pF
Operating Junction Temperature	T_J	125			$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +125			$^\circ\text{C}$



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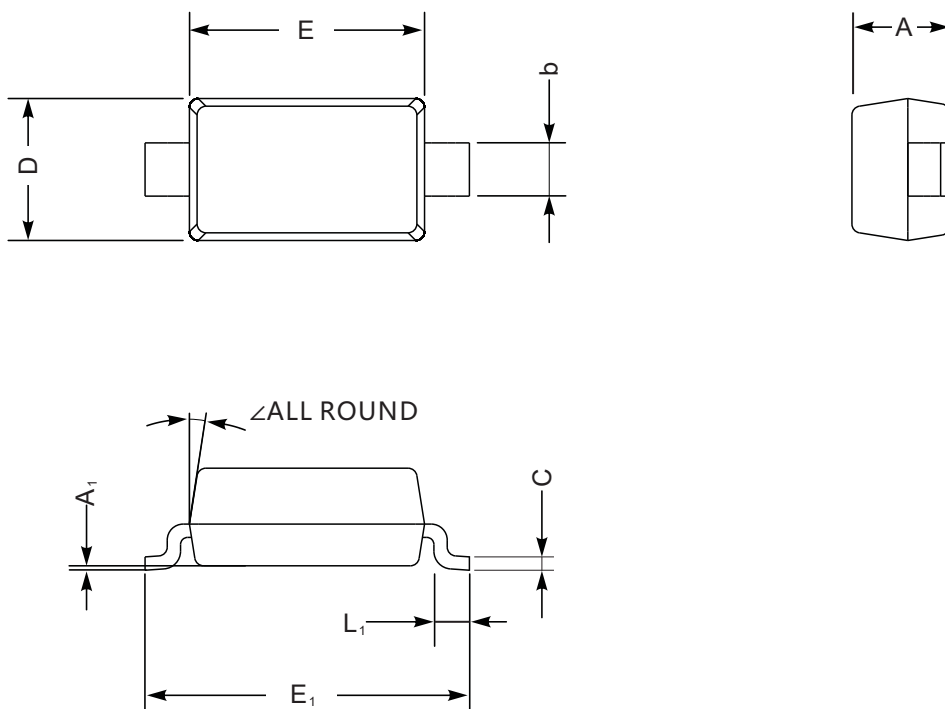
Typical Characteristic Curves



Package Outline

SOD-123

Dimensions in mm



SOD-123 mechanical data

UNIT		A	C	D	E	E ₁	L ₁	b	A ₁	∠
mm	max	1.3	0.22	1.8	2.8	3.9	0.45	0.7	0.2	9°
	min	0.9	0.09	1.5	2.5	3.6	0.25	0.5	—	
mil	max	51	8.7	71	110	154	18	28	8	
	min	35	3.5	59	98	142	10	20	—	